

In the Claims:

1. (Previously Presented) An electronic component comprising:
  - a wafer;
  - a plurality of bond pads disposed on a surface of the wafer;
  - a plurality of functional 3-D structures disposed on the surface of the wafer, such that each bond pad is laterally spaced from the plurality of bond pads so that each bond pad is associated with a laterally-spaced one of the 3-D structures, each functional 3-D structure including a non-conductive compliant base element and having an upper surface spaced from the surface of the wafer;
  - a plurality of reroute traces, each reroute trace extending over the surface of the wafer between a bond pad and its associated 3-D structure such that each reroute trace is electrically connected to one of the bond pads and extends onto the upper surface of the associated laterally-spaced one of the functional 3-D structures so that the reroute trace provides an electrical connection between the bond pad and the upper surface of the associated functional 3-D structure; and
  - a plurality of selected 3-D structures disposed on the surface of the wafer to provide a mechanical reinforcement, wherein at least some of the selected 3-D structures have a greater mechanical load-bearing capacity than some of the functional 3-D structures.
2. (Original) The component of claim 1 wherein each reroute trace comprises a copper/nickel layer that is covered by a gold layer.
3. (Original) The component of claim 1 wherein the selected 3-D structures have a lower degree of compressibility than the functional 3-D structures.

4. (Previously Presented) The component of claim 1 wherein the selected 3-D structures have a greater height than the functional 3-D structures.

5. (Previously Presented) The component of claim 1 wherein each of the selected 3-D structures includes a compliant base element that has a greater volume than the compliant base element of the functional 3-D structures.

6-7. (Cancelled)

8. (Original) The component of claim 1 wherein the selected 3-D structures are arranged in a regularly distributed manner in an edge region of the wafer.

9. (Original) The component of claim 1 wherein the selected 3-D structures are arranged in a regularly distributed manner over the wafer.

10. (Original) The component of claim 1 wherein the selected 3-D structures are able to be electrically bonded.

11.-33. (Cancelled)

34. (Previously Presented) The electronic component of claim 1, wherein the compliant base element is formed from silicone.